

## IN THE SPECIFICATION

Following is a marked-up version of each amended paragraph of the subject patent application. The Examiner is requested to delete the indicated paragraph and replace it with the amended paragraph. The location for each of the deleted and replaced paragraphs is also indicated.

Amend the paragraph beginning on page 6, line 10 and ending on page 6, line 11 with the following.

Figures 3 ~~through 6~~ illustrates, in cross-section, a prior art first implanting step, one step in a process for forming MOSFETs with different threshold voltages. ~~during sequential processing steps.~~

Add the following paragraphs following line 11 on page 6.

Figure 4 illustrates, in cross-section, a prior art second implanting step, one step in a process for forming MOSFETs with different threshold voltages.

Figure 5 illustrates, in cross-section, a prior art third implanting step, one step in a process for forming MOSFETs with different threshold voltages.

Figure 6 illustrates, in cross-section, a prior art fourth implanting step, one step in a process for forming MOSFETs with different threshold voltages.

Amend the paragraph beginning on page 6, line 13 and ending on page 6, line 15 with the following

Figures 9 ~~through 17~~ illustrates, in cross-section, an implanting step, one step in a process for forming MOSFETs with different threshold voltages according to the teachings of the present invention.

Add the following paragraphs following line 11 on page 15.

Figure 10 illustrates, in cross-section, doped wells formed according to the implant step of Figure 9.

Figure 11 illustrates, in cross-section, a tilted implanting step, one step in a process for forming MOSFETs with different threshold voltages according an embodiment of the present invention.

Figures 12A and 12B illustrate, in cross-section, a tilted implanting step and dopant profiles associated therewith according to an embodiment of the present invention.

Figures 13A and 13B illustrate, in cross-section, a tilted implanting step and dopant profiles associated therewith according to the another embodiment of the present invention.

Figure 14 illustrates, in cross-section, a mirror image implanting step with respect to the implanting step of Figure 11, for forming MOSFETs with different threshold voltages according to an embodiment of the present invention.

Figures 15A and 15B illustrate, in cross-section, a halo implanting step and dopant profiles associated therewith.

Figures 16A and 16B illustrate, in cross-section, an halo implanting step and dopant profiles associated therewith according to an embodiment of the present invention.

Figures 17A, 17B and 17C illustrate, in cross-section, a halo implanting step and dopant profiles associated therewith according to an embodiment of the present invention.